

## CLAIMS

What is claimed is:

1. An apparatus comprising:  
a contact point formed on a device layer of a circuit substrate or interconnect layer on the substrate;  
a first dielectric layer comprising cubic boron nitride on the substrate; and  
a different second dielectric layer on the substrate and separated from the device layer by the first dielectric layer.
2. The apparatus of claim 1, wherein collectively the first dielectric layer and the second dielectric layer comprise a composite dielectric layer having a composite dielectric constant value less than 3.0.
3. The apparatus of claim 2, wherein the contribution of the first dielectric layer to the composite dielectric constant value is up to 20 percent.
4. The apparatus of claim 1, further comprising a third dielectric layer on the substrate such that the second dielectric layer is between the first dielectric layer and the third dielectric layer and collectively the layers define a composite dielectric layer, wherein the third dielectric layer comprises a material having a dielectric constant similar to the material of the first dielectric layer.
5. The apparatus of claim 4, further comprising a contact through the composite dielectric layer.
6. The apparatus of claim 5, wherein the contact has a body with a length dimension extending through the composite dielectric layer and the third dielectric

material is formed on the length dimension of the body between the contact and the second dielectric layer.

7. The apparatus of claim 6, wherein the material of the third dielectric layer comprises cubic boron nitride.

8. An apparatus comprising:  
a circuit substrate comprising a device layer; and  
a composite dielectric layer formed on the circuit substrate comprising:  
a first dielectric material comprising cubic boron nitride, and  
a different second dielectric material,  
wherein the first dielectric material surrounds the second dielectric material.

9. The apparatus of claim 8, wherein the composite dielectric has a dielectric constant value less than 3.0.

10. The apparatus of claim 9, wherein the contribution of the first dielectric layer to the composite dielectric constant value is up to 20 percent.